

ABSTRACT

A back-illuminated image sensor has a converting layer 21, charge collecting portions 24, and suppressing regions 23 and 29. The converting layer 21 for converting an incident beam into signal charges is formed on one side of an incident face 8 on which an incident beam is irradiated. The converting layer 21 is provided for each of pixels arranged in two dimensions. The charge collecting portions 24 for collecting signal charges generated in the converting layer 21 extends from the converting layer 21 to a surface 22 opposite to the incident face 8. The suppressing regions 23 and 29 for suppressing the flow of the signal charges from the converting layer 21 to peripheral circuits 26 is formed between the converting layer 21 and the peripheral circuits 26.